

# EE5323

## VLSI Design I

Kia Bazargan

University of Minnesota  
Dept. of ECE

[kia@umn.edu](mailto:kia@umn.edu)  
[www.ece.umn.edu/users/kia](http://www.ece.umn.edu/users/kia)

Slides Adapted from Prof. Chris Kim's F07 offering of the course

## Course Information

- **Class webpage**
  - <http://www.ece.umn.edu/users/kia/Courses/EE5323>
- **Instructor: *Kia Bazargan***
  - Office: EE/CSci 4-159, Email: [kia@umn.edu](mailto:kia@umn.edu)
  - Ph: (612) 625 4588
  - *Office hrs*: MW 10-11, or by appointment
- **TA: *Satish Sivaswamy***
  - Office: VLSI Lab EE/CSci 1-200, Email: [satish@umn.edu](mailto:satish@umn.edu)
  - Ph: (612) 626 7163
  - *Lab/office hrs*: TTh 11-12
- **UNITE / WebVista webpage**
  - [www.myu.umn.edu](http://www.myu.umn.edu)

## UNITE

- **Class will be broadcast through the UNITE system**
- **Streaming video available**
  - [www.myu.umn.edu](http://www.myu.umn.edu)
  - Please attend class for more interaction
- **To encourage your attendance, video will be available 10 days after the actual lecture (standard UNITE policy – no exceptions)**

## Class Material

- **Textbook:**
  - “Digital Integrated Circuits – A Design Perspective”, 2<sup>nd</sup> ed, by J. Rabaey, A. Chandrakasan, B. Nikolic
- **Writing on the board versus powerpoint**
- **Other references**
  - I. E. Sutherland, R. F. Sproull, and D. F. Harris, Logical effort : Designing fast CMOS circuits, Morgan Kaufmann, San Francisco, CA, 1999.
  - Y. Taur, T. Ning, Fundamentals of Modern VLSI Devices, Cambridge University Press, 2002.

## CAD Software

- **Cadence schematic and layout**
  - Industry standard
  - Online tutorials
  - Companies prefer to hire students with design experience in Cadence environment (making you competitive for industry jobs is a big focus of this class)
- **HSPICE for circuit simulation**
- **Cosmoscope for viewing results**
- **Technology file: 140nm**
- **VLSI lab: EE/CSci 1-200**
- **Off-campus students can use your company's tools**

## Academic Integrity

- **Students caught engaging in an academically dishonest practice will receive a failing grade for the course.**
- **University policy on academic dishonesty will be followed strictly.**
  - <http://www1.umn.edu/oscai/>

## Policies

- **Homework must be received before class**
  - 3 days of grace period to be used for all assignments (e.g., 1 day each for 3 assignments, or 3 days on one assignment)
  - After the grace period is used up, late submission results in a zero grade
- **Zero tolerance for cheating**
- **Collaboration OK, copying NOT OK**
- **No extra work for extra credit**
- **Check class web pages regularly. Students are responsible for checking their email, the discussion threads and the announcements section on class web page regularly**

## Grading Policy

- **20% Homework and quizzes**
- **20% final project**
  - **Two phases**
  - **Requires a lot of time**
- **25% Midterm - open notes, open book.**
- **35% Final exam - open notes, open book**

## Action Required

- **Subscribe to the class email list**
  - Instructions on class website
- **Read the definition of academic integrity at:**  
<http://www1.umn.edu/oscai/>

## VLSI Area Courses at the U

### VLSI CAD

**EE 5301**  
VLSI Design  
Automation I

**EE 5302**  
VLSI Design  
Automation II

### VLSI Circuits

**EE 5323**  
VLSI Design I

**EE 5324**  
VLSI Design II

**EE 5333**  
Analog  
Integrated Circuit  
Design

### Others

**EE 5327**  
VLSI Design Lab

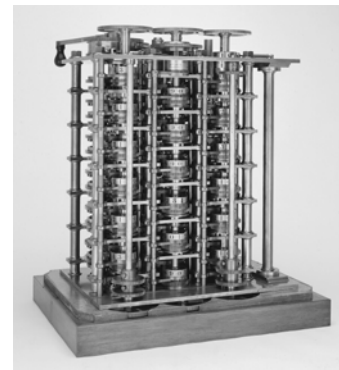
**EE 5329**  
VLSI Digital  
Signal Processing  
Systems

- **Plus a wide variety of 8000 level courses**

## Course Overview

- This class is intended to be an introduction to the design of very large scale integrated (VLSI) circuits. It is the first part of a two-semester sequence: this part focuses on the transistor-level and logic-level aspects, while the second part, EE 5324, concentrates on designing circuits that implement various functionalities (e.g. memories, datapath units).
- The main objective of the two-semester sequence is to provide the student with the capability of designing digital VLSI circuits.

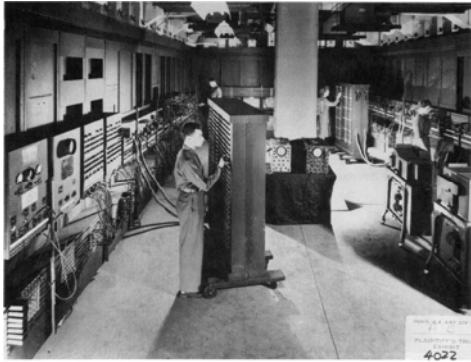
## The First Computer



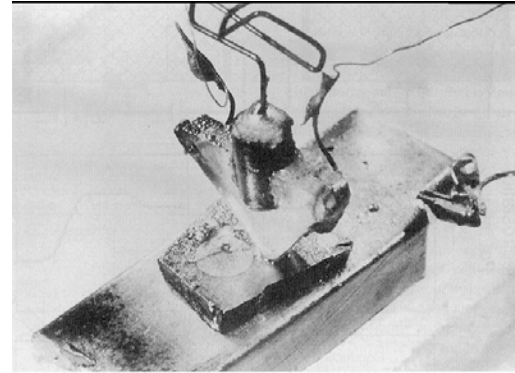
**The Babbage  
Difference Engine  
(1832)**

**25,000 parts  
cost: £17,470**

## ENIAC - The First Electronic Computer (1946)

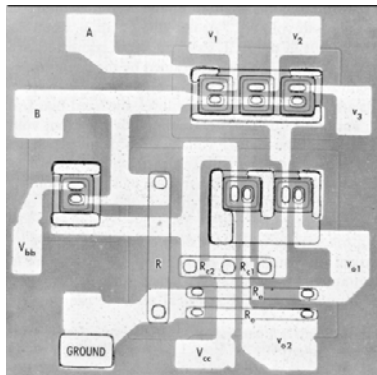


## The Transistor Revolution



First transistor  
Bell Labs, 1948

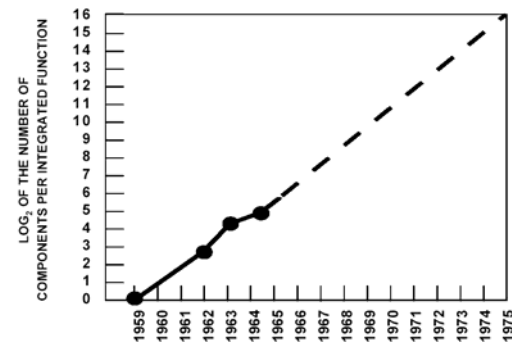
## The First Integrated Circuits



*Bipolar logic*  
1960's

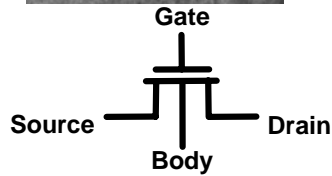
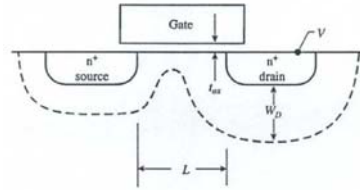
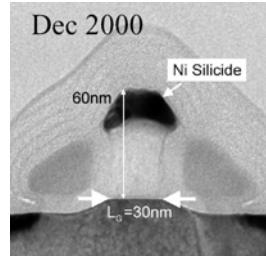
ECL 3-input Gate  
Motorola 1966

## Moore's Law



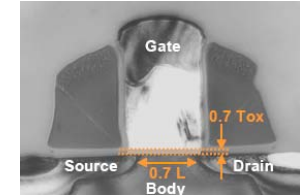
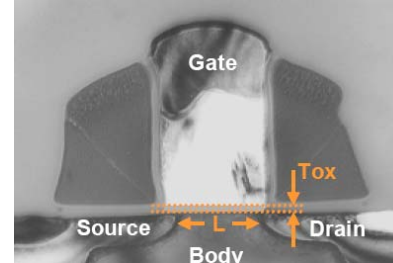
- Intel founder and chairman Gordon Moore predicted in 1965 that the number of transistors on a chip will double every 18-24 months

# MOS Transistor



Kuroda, IEDM panel

# Transistor Scaling



- Constant Voltage Scaling
- Constant E-field Scaling

# Good Old Days: Intel Processors

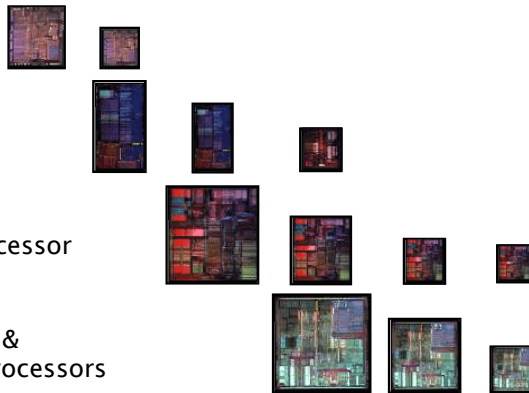
Silicon Process Technology 1.5μ 1.0μ 0.8μ 0.6μ 0.35μ 0.25μ

Intel386™ DX Processor

Intel486™ DX Processor

Pentium® Processor

Pentium® Pro & Pentium® II Processors



Source: <http://www.intel.com/>

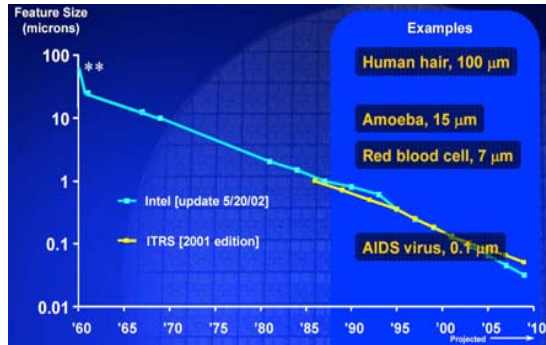
# ITRS Roadmap

ITRS roadmap (2002)

Year	2001	2003	2005	2007	2010	2013	2016
DRAM 1/2 pitch [nm]	130	100	80	65	50	32	22
MPU transistors/chip	97M	153M	243M	386M	1.1B	1.55G	3.09G
Wiring levels	8	8	10	10	10	11	11
High-perf. phys. gate [nm]	65	45	32	25	20	15	9
High-perf. VDD [V]	1.2	1.0	0.9	0.7	1 V	0.8	0.4
Local clock [GHz]	1.7	3.1	5.2	6.7	2 GHz	5	28.8
High-perf. power [W]	130	150	170	190	218	251	288
Low-power phys. gate [nm]	90	65	45	32	22	16	11
Low-power VDD [V]	1.2	1.1	1.0	0.9	0.8	0.7	0.6
Low-power power [W]	2.4	2.8	3.2	3.5	3.0	3.0	3.0

- International Technology Roadmap for Semiconductors 2002 projection (<http://public.itrs.net/>)

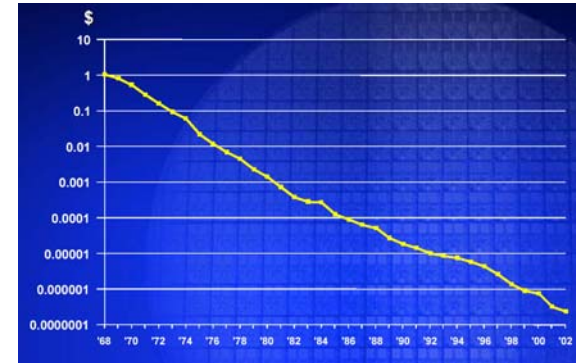
## Transistor Scaling



- 45nm is getting ready for production, 32nm is in research phase
- New technology generation introduced every 2-3 years

21

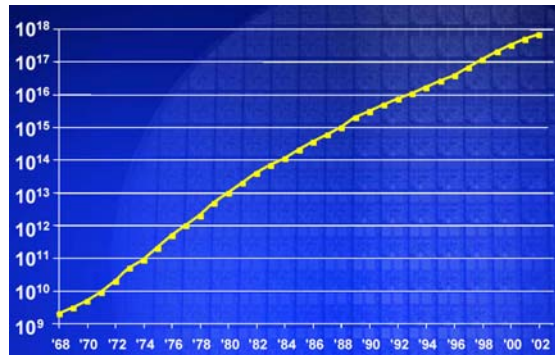
## Cost per Transistor



- You can buy 10M transistors for a buck
- They even throw in the interconnect and package for free

22

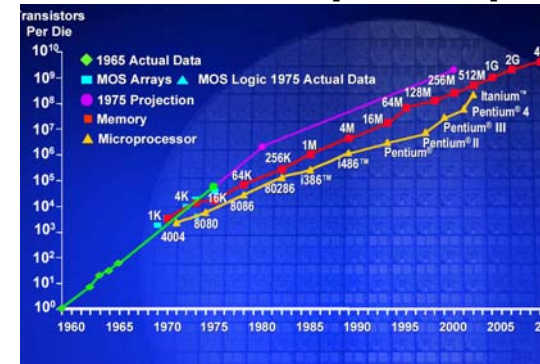
## Transistors Shipped Per Year



- Today, there are about 100 transistors for every ant  
- Gordon Moore, ISSCC '04

23

## Transistors per Chip



- 1.7B transistors in Montecito (next generation Itanium)
- Most of the devices used for on-die cache memory

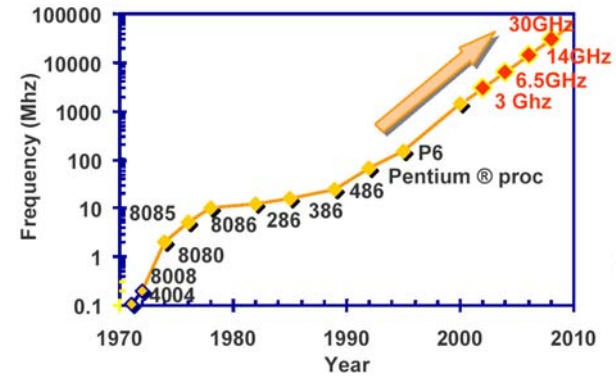
24

## Moore's Wrong Prediction



25

## Chip Frequency

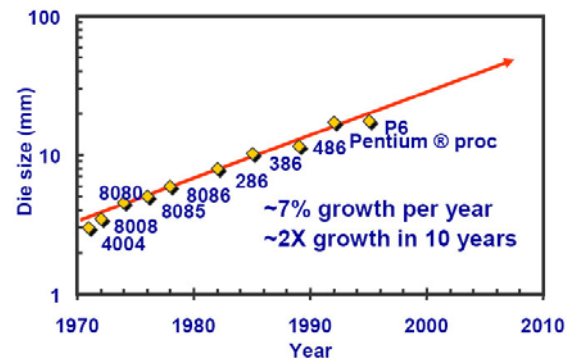


S. Borkar

- 30% higher frequency every new generation

26

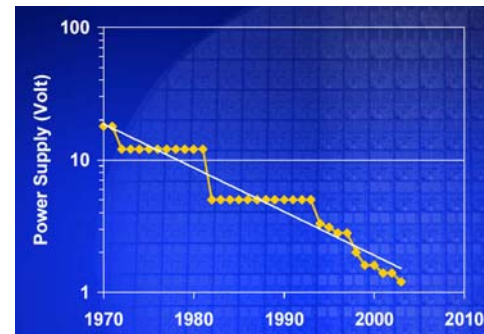
## Die Size



- ~15% larger die every new generation
- This means more than 2X increase in transistors per chip

27

## Supply Voltage Scaling

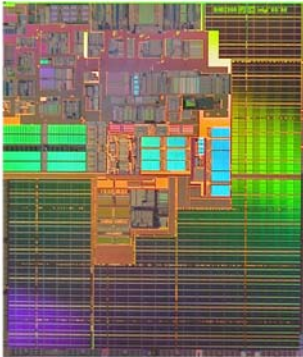


- Supply voltage is decreased for power reduction

$$P_{active} \propto C V_{dd}^2 f$$

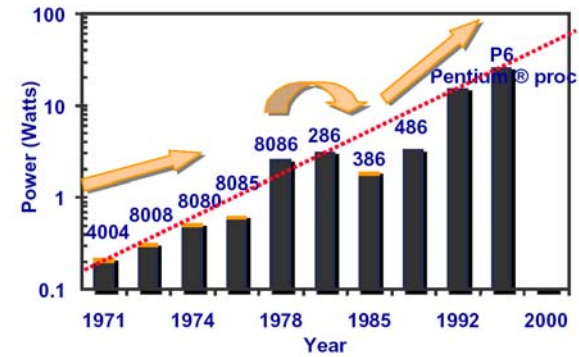
28

## 4 Decades of Transistor Scaling: Itanium 2 Processor



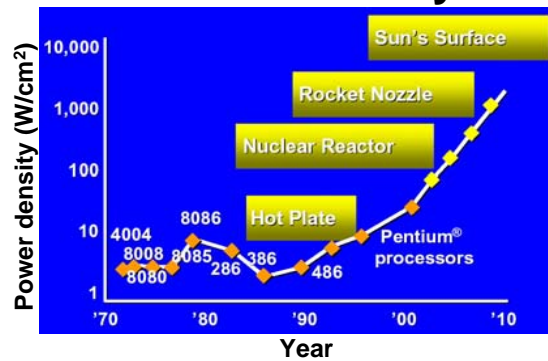
- 130nm process
- 410M transistors
- 374mm<sup>2</sup> die size
- 6MB on-die L3 cache
- 1.5GHz at 1.3V
- 6.4GB/s 400MT/s 4-way bus interface
- System compatible with existing Itanium 2 platforms
- Extensive RAS, DFT and DFM features

## Power



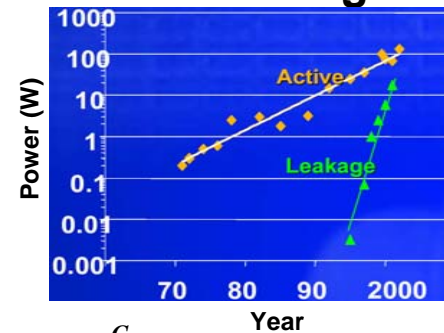
- Lead microprocessors power continues to increase

## Power Density



- High-end microprocessors: Packaging, cooling
- Mobile/handheld applications: Short battery life

## Active and Leakage Power



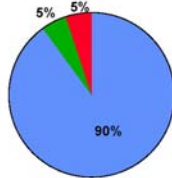
$$delay \propto \frac{C_L}{1 - V_t/V_{dd}} \quad I_{leak} \propto \exp\left(\frac{-V_t}{mkT/q}\right)$$

- Transistors are becoming dimmers

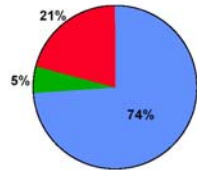


## Leakage Power Crawling Up in Itanium 2

- Same thermal design envelope as the 180nm Itanium® 2 processor
  - 50% frequency increase
  - 2X larger L3 cache
  - Leakage increased 3.5X



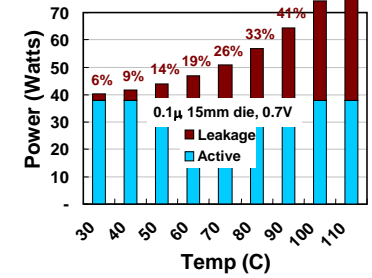
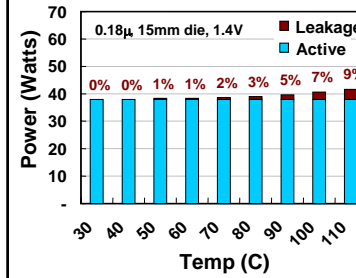
Itanium® 2 Processor 3M (180nm)



Itanium® 2 Processor 6M (130nm)

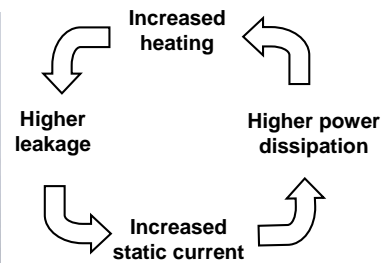
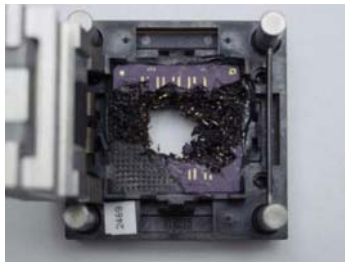
- Transistor leakage is perhaps the biggest problem

## Leakage Power versus Temp.



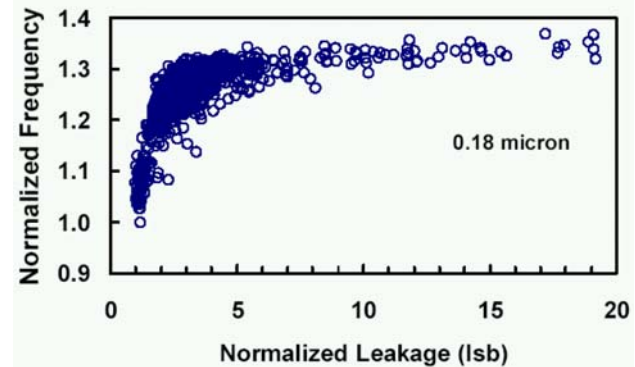
- Leakage power is problematic in active mode for high performance microprocessors

## Thermal Runaway



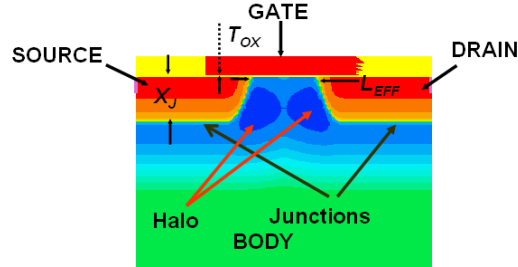
- Destructive positive feedback mechanism
- Leakage increases exponentially with temperature
- May destroy the test socket → thermal sensors required

## Process Variation in Microprocessors



- Fast chips burn too much power
- Slow chips cannot meet the frequency requirement

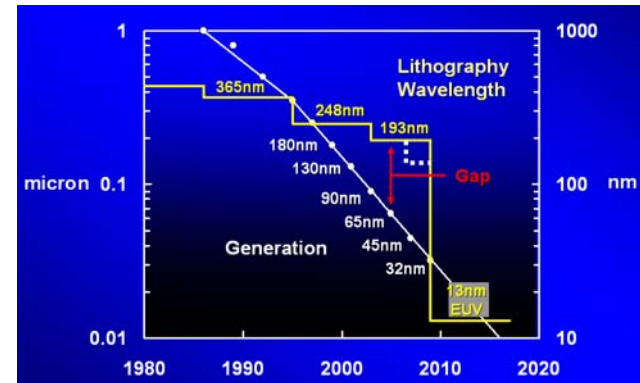
## Sources of Process Variation



- Intrinsic parameter variation (static)
  - Channel length, random dopant fluctuation
- Environmental variation (dynamic)
  - Temperature, supply variations

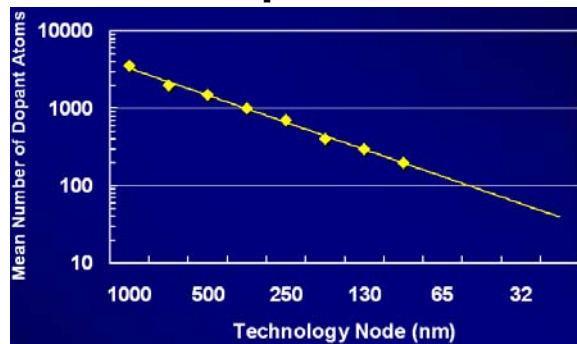
37

## Sub-wavelength Lithography



38

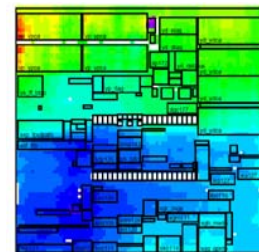
## Random Dopant Fluctuation



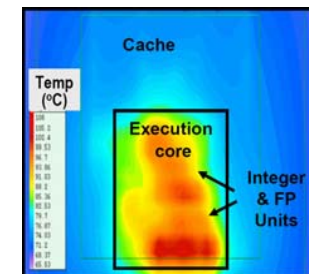
- $V_t$  variation caused by non-uniform channel dopant distribution

39

## Voltage and Temperature Variations



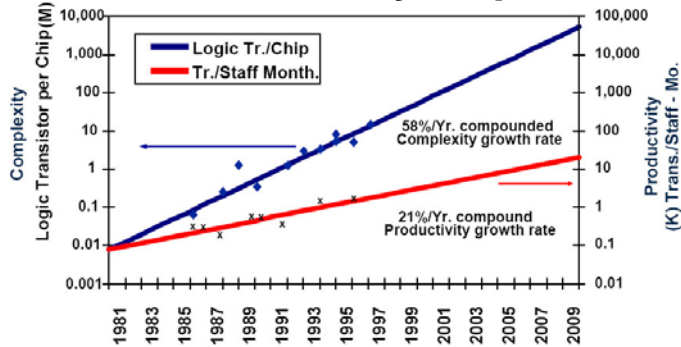
- IR, Ldi/dt noise



- Hotspot
- Thermal runaway

40

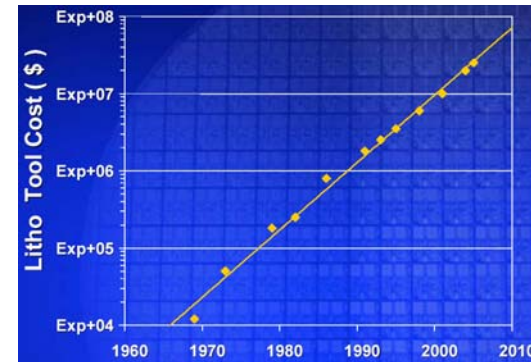
## Productivity Gap



- Design complexity surpasses manpower
- Effective CAD tools, memory dominated chips

41

## Lithography Tool Cost



- What will end Moore's law, economics or physics?

42

## Summary

- Digital IC Business is Unique
  - Things Get Better Every Few Years
  - Companies Have to Stay on Moore's Law Curve to Survive
- Benefits of Transistor Scaling
  - Higher Frequencies of Operation
  - Massive Functional Units, Increasing On-Die Memory
  - Cost/MIPS Going Down
- Downside of Transistor Scaling
  - Power (Dynamic and Static)
  - Process Variation
  - Design/Manufacturing Cost
  - ....

43